

2SA633

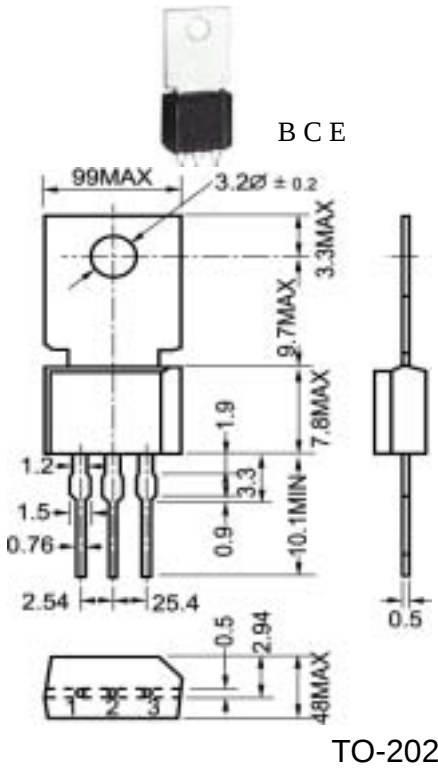
Silicon PNP Transistors

◆ Features

. With TO-202 package

◆ Absolute Maximum Ratings Tc=25℃

SYMBOL	PARAMETER	RATING	UNIT
V _{CBO}	Collector to base voltage	30	V
V _{CEO}	Collector to emitter voltage	30	V
V _{EBO}	Emitter to base voltage	5.0	V
I _B	Base collector current		A
I _C	Collector current	2.0	A
P _C	Collector power dissipation	10	W
T _j	Junction temperature	150	℃
T _{stg}	Storage temperature	-55~+150	℃



◆ Electrical Characteristics Tc=25℃

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
I _{CBO}	Collector-base cut-off current	V _{CB} =30V; I _E =0			100	uA
I _{EBO}	Emitter-base cut-off current	V _{EB} =5.0V; I _C =0			100	uA
I _{CEO}	Collector-emitter cut-off current	V _{CE} =30V; I _B =0			0.5	mA
V _{CBO}	Collector-base breakdown voltage					
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =20mA; I _B =0	30			V
V _{EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	5			
V _{CE(sat-1)}	Collector-emitter saturation voltages	I _C =1.5A; I _B =0.15A			1.0	V
V _{CE(sat-2)}	Collector-emitter saturation voltages					
h _{FE-1}	Forward current transfer ratio	I _C =1A; V _{CE} =5V	80			
h _{FE-2}	Forward current transfer ratio					
h _{FE-3}	Forward current transfer ratio					